

etching the first mask pattern by an isotropic dry etching so as to form a second mask pattern, wherein the isotropic dry etching is carried out with plasma dry etching equipment,

• which uses a microwave energy source;

removing the insulating layer by a first anisotropic dry etching using the second mask pattern;

removing the second mask pattern; and

etching the conducting layer by a second anisotropic dry etching using the remaining insulating layer, so as to form the bit line.

5. (Amended) The method as claimed in claim 1, wherein the isotropic dry etching is carried out while oxygen gas is supplied.

9. (Amended) The method as claimed in claim 1, wherein the isotropic dry etching is carried out using a source of power of less than 400 Watts.

10. (Amended) The method as claimed in claim 1, wherein the isotropic dry etching is carried out using a source of power of 200 to 300 Watts.

11. (Amended) The method as claimed in claim 1, wherein the isotropic dry etching is carried out using a pressure of 600 to 1000 mT.

Please add the following claim:

--15. (New) A method of manufacturing a bit line having a width of not more than 0.1 μm , the method comprising the steps of:

successively forming a conducting layer and an insulating layer on a substrate;
forming a photoresist film on the insulating layer;
patterning the photoresist film using a photolithography process such that a desired region of the insulating layer is exposed to form a first photoresist pattern having a width of at least 0.14 μm ;

 partially removing the first photoresist pattern by an isotropic dry etching process so as to form a second photoresist pattern having a width of not more than 0.1 μm , said isotropic dry etching process being carried out by supplying oxygen gas at a flow rate of approximately 800 sccm, using a microwave energy source having a power less than 400 Watts and at a pressure of approximately 600 to 1,000 mT;

removing a portion of said insulating layer by a first anisotropic dry etching using the second photoresist pattern as a mask, a remaining portion of said insulating layer forming a hard mask;

removing the second photoresist pattern; and
etching the conducting layer by a second anisotropic dry etching using the hard mask so as to form the bit line, said bit line having a same shape as said second photoresist pattern such that said bit line has a width of not more than 0.1 μm --